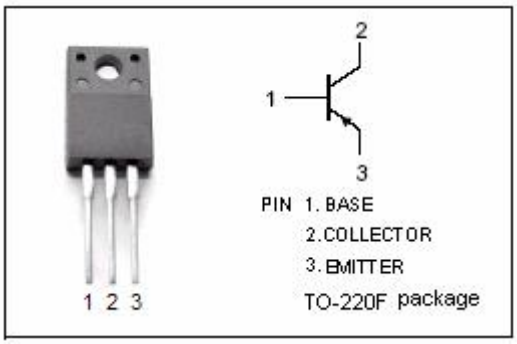
SPTECH Silicon PNP Power Transistor

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : V_{CEO}= -60V(Min)
- High DC Current Gain-
  : h_{FE}= 100(Min)@ (V_{CE}= -2V , I_C= -1A)
- Low Saturation Voltage-
  : $V_{CE(sat)}$= −0.3V(Max)@ (I_C= -3A, I_B= -0.15A)

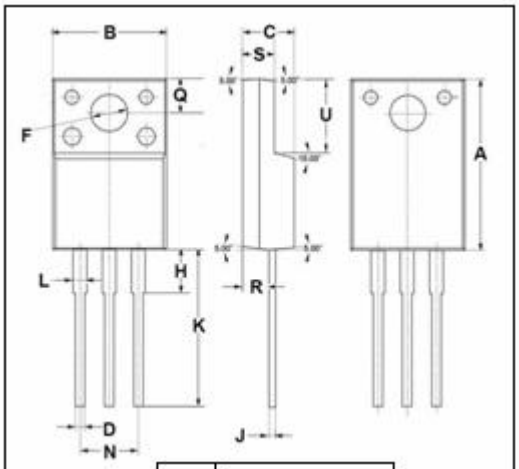


APPLICATIONS

- This type of power transistor is developed for high-speed switching and features a high h_{FE} at low $V_{CE(sat)}$,which is ideal for use as a driver in DC/DC converters and actuators.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7.0	V
I_C	Collector Current-Continuous	-7.0	A
I_{CM}	Collector Current-Pulse	-12	A
I_B	Base Current-Continuous	-2.5	A
P_T	Total Power Dissipation @T_C=25℃	25	W
	Total Power Dissipation @T_a=25℃	2.0	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

SPTECH Silicon PNP Power Transistor

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-Emitter Voltage	I_C= -10mA; I_B= 0	-60			V
V_{CBO}	Collector-Emitter Voltage	I_E= -1mA; I_C= 0	-100			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.15A			-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.2A			-0.5	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= -3A; I_B= -0.15A			-1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= -4A; I_B= -0.2A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V ; I_E=0			-10	μA
I_{CEO}	Collector Cutoff Current	V_{CE}= -50V; I_B=0			-1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -0.5A ; V_{CE}= -2V	100			
h_{FE-2}	DC Current Gain	I_C= -1.0A ; V_{CE}= -2V	100		400	
h_{FE-3}	DC Current Gain	I_C= -3.0A ; V_{CE}= -2V	60			
Switching times						
t_{on}	Turn-on Time	I_C= -3.0A ,R_L= 17Ω , I_{B1}= -I_{B2}= -0.15A,V_{CC}≈-50V			0.3	μs
t_{stg}	Storage Time				1.5	μs
t_f	Fall Time				0.3	μs

◆ h_{FE-2} Classifications

M	L	K
100-200	150-300	200-400